

METHOD AND SYSTEM FOR IMPROVING PERFORMANCE OF MOSFETS

ABSTRACT OF THE DISCLOSURE

According to one embodiment of the invention, a method for forming MOSFETs includes providing a substrate having a source region, a gate region, and a drain region, forming a silicon-germanium layer in each of the source and drain regions, forming, in the substrate, a source in the source region and a drain in the drain region, forming a silicon layer outwardly from the silicon-germanium layer in each of the source and drain regions, and forming a silicide layer in each of the source and drain regions.